

MOSFET

OptiMOS™ Power Transistor, -60 V

Features

- P-Channel
- Very low on-resistance $R_{DS(on)}$ @ $V_{GS}=4.5$ V
- 100% avalanche tested
- Logic Level
- Enhancement mode
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

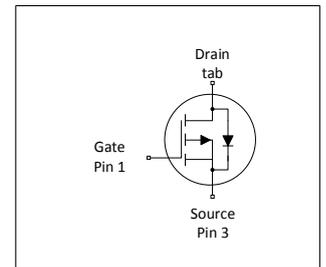


Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	-60	V
$R_{DS(on),max}$	250	$m\Omega$
I_D	-6.5	A



Type / Ordering Code	Package	Marking	Related Links
IPD25DP06LM	PG-TO 252-3	25DP06LM	-

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1 Maximum ratings

at $T_C=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	-6.5 -5.0 -6.4 -4.5	A	$V_{GS}=-10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=-10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=-4.5\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=-4.5\text{ V}$, $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	-26	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	75	mJ	$I_D=-6.5\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	28	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j , T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	R_{thJC}	-	-	5.3	°C/W	-
Device on PCB, 6 cm ² cooling area ³⁾	R_{thJA}	-	-	75	°C/W	-

¹⁾ See Diagram 3 for more detailed information

²⁾ See Diagram 13 for more detailed information

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	-60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=-250\text{ }\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-1	-1.5	-2	V	$V_{DS}=V_{GS}$, $I_D=-270\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	-0.1 -10	-1 -100	μA	$V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=-60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	-10	-100	nA	$V_{GS}=-20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	187 230	250 310	m Ω	$V_{GS}=-10\text{ V}$, $I_D=-6.5\text{ A}$ $V_{GS}=-4.5\text{ V}$, $I_D=-6.4\text{ A}$
Gate resistance	R_G	-	5	-	Ω	-
Transconductance	g_{fs}	-	8.4	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=-6.5\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	420	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	60	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	15	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=-30\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	3	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-3.25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r	-	6	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-3.25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	22	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-3.25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Fall time	t_f	-	3	-	ns	$V_{DD}=-30\text{ V}$, $V_{GS}=-10\text{ V}$, $I_D=-3.25\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$

Table 6 Gate charge characteristics¹⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	-1.5	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	-0.6	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate to drain charge	Q_{gd}	-	-3.9	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Switching charge	Q_{sw}	-	-4.8	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate charge total	Q_g	-	-13.8	-	nC	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	-3.7	-	V	$V_{DD}=-30\text{ V}$, $I_D=-6.5\text{ A}$, $V_{GS}=0\text{ to }-10\text{ V}$
Output charge	Q_{oss}	-	-4.4	-	nC	$V_{DD}=-30\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ See diagram ,Gate charge waveforms, for gate charge parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	-6.5	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	-26	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	-0.9	-1.2	V	$V_{GS}=0\text{ V}, I_F=-6.5\text{ A}, T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	37	-	ns	$V_R=-30\text{ V}, I_F=-6.5\text{ A}, di_F/dt=-100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	-63	-	nC	$V_R=-30\text{ V}, I_F=-6.5\text{ A}, di_F/dt=-100\text{ A}/\mu\text{s}$

4 Electrical characteristics diagrams

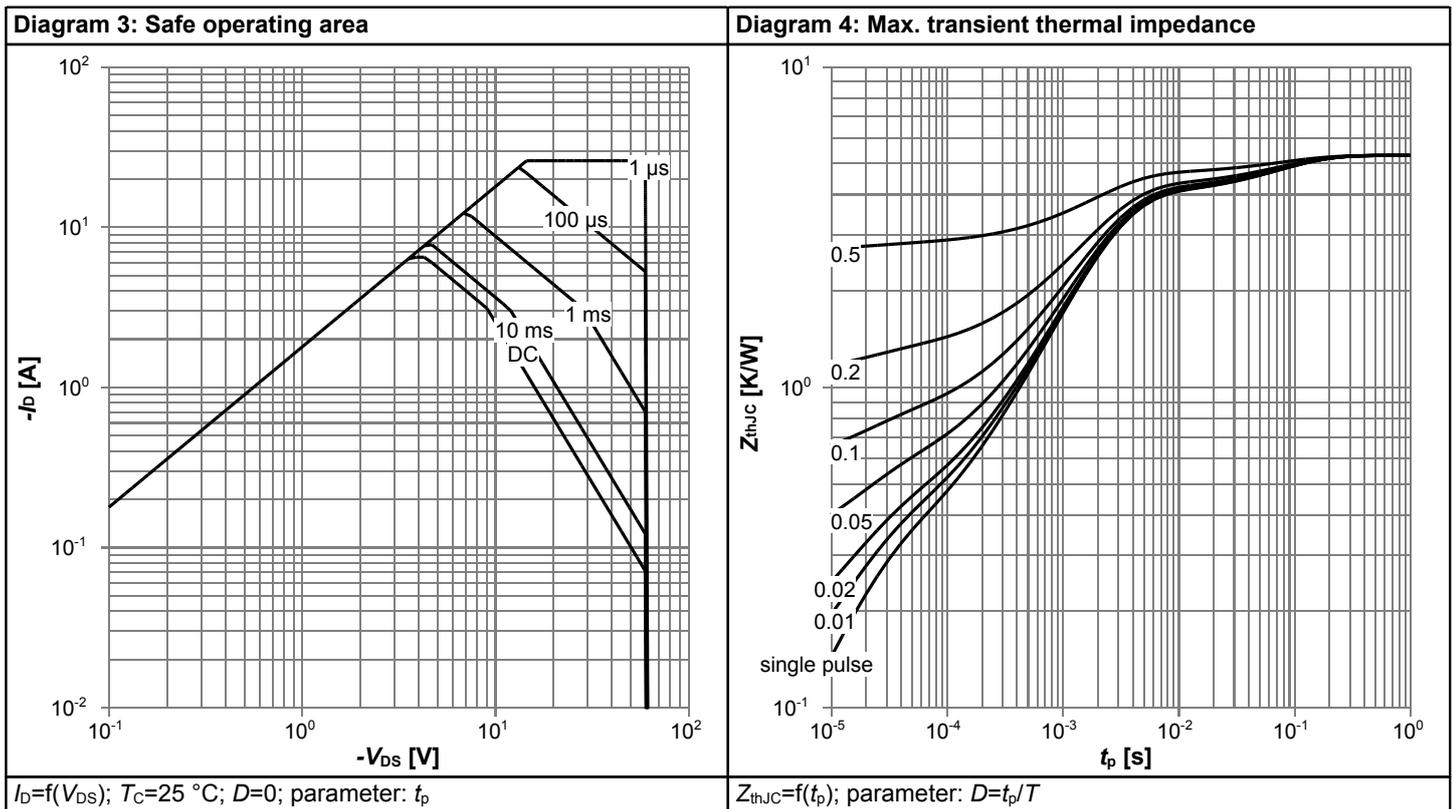
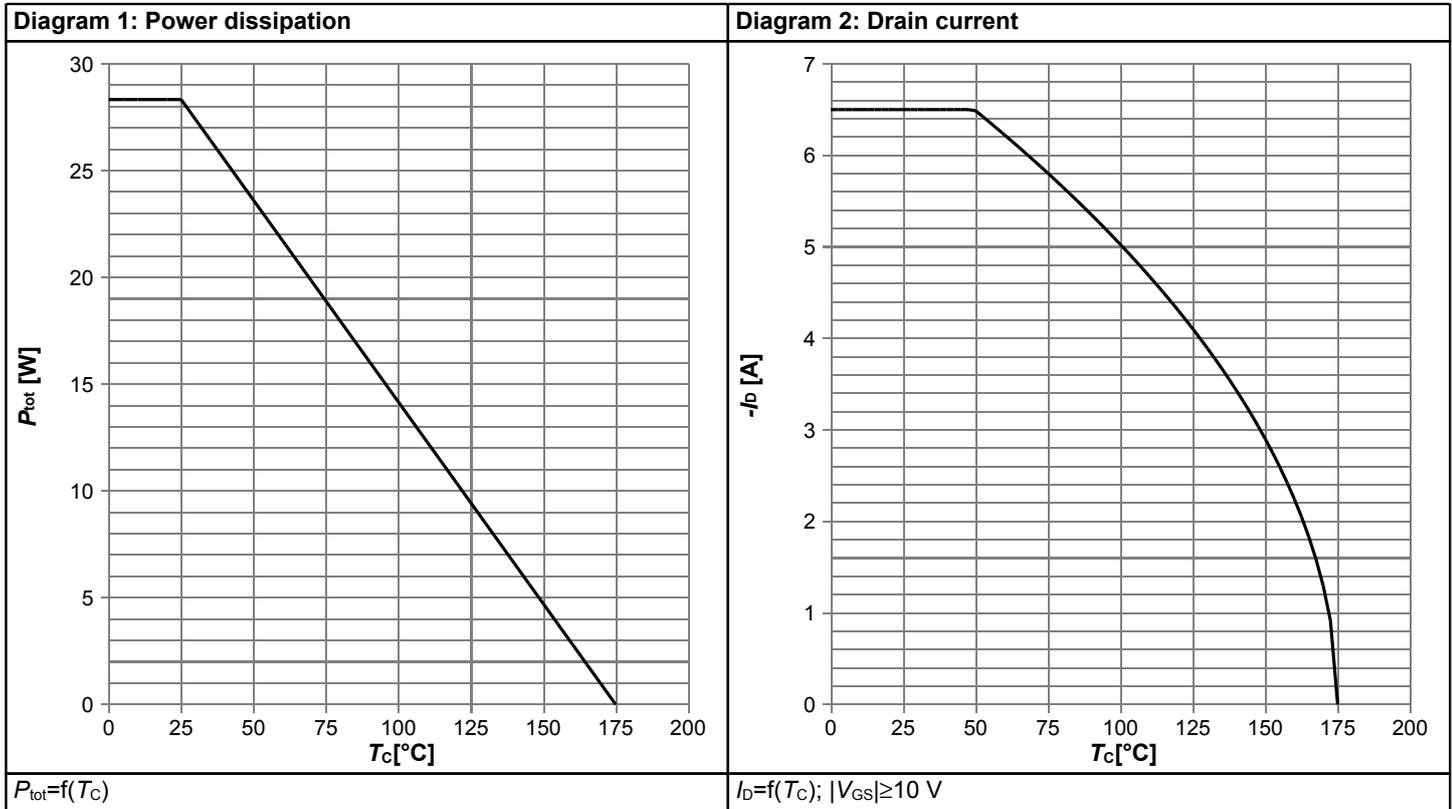
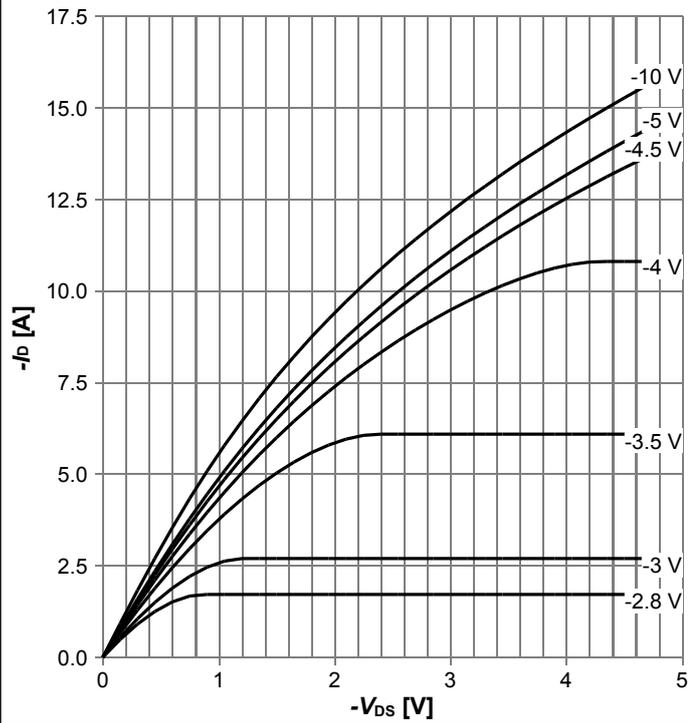
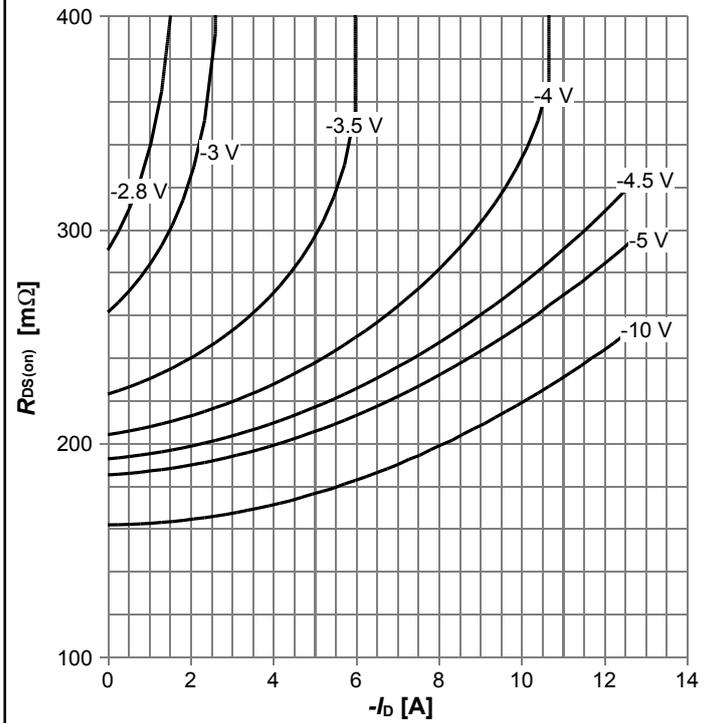


Diagram 5: Typ. output characteristics



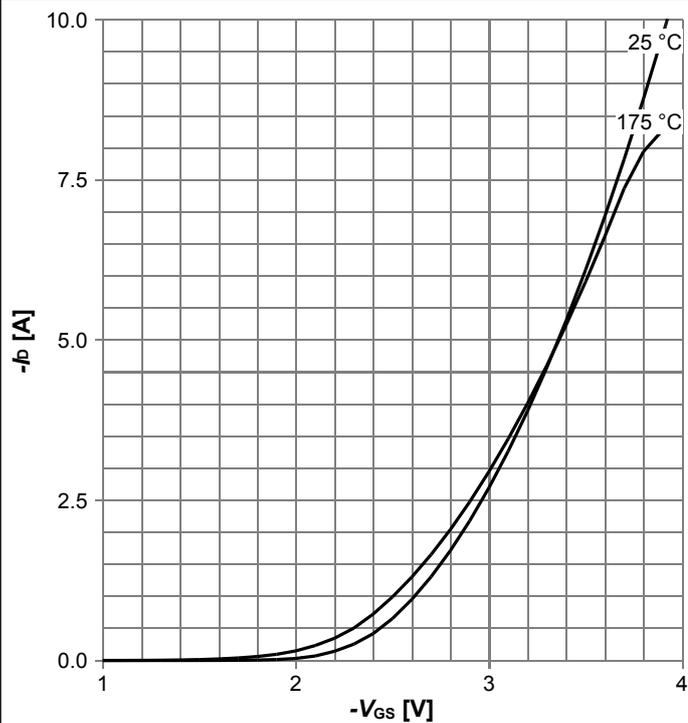
$I_D=f(V_{DS})$, $T_j=25\text{ }^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



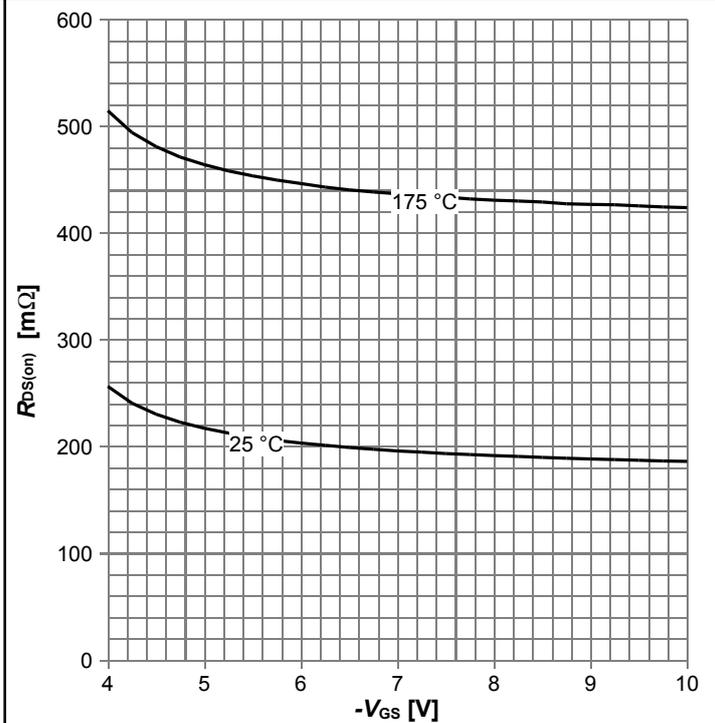
$R_{DS(on)}=f(I_D)$, $T_j=25\text{ }^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



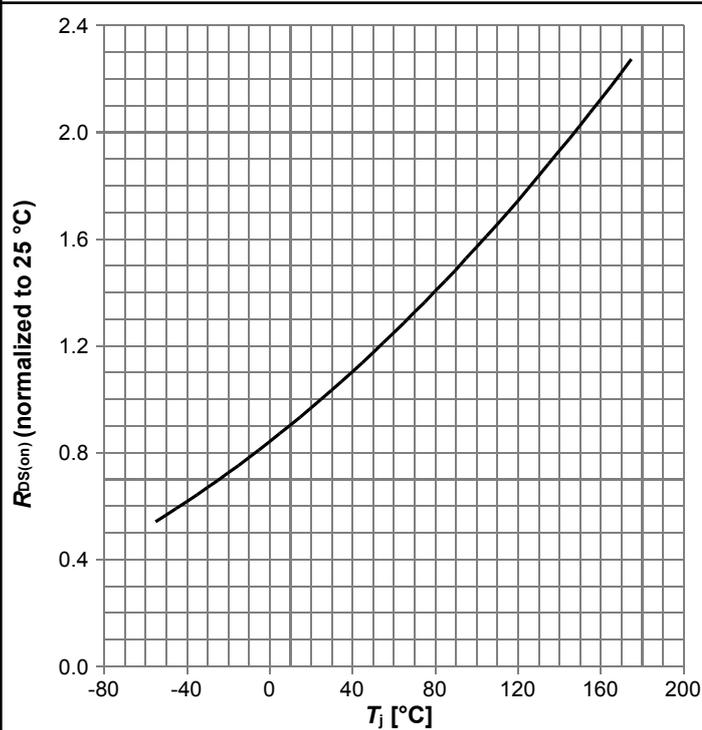
$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



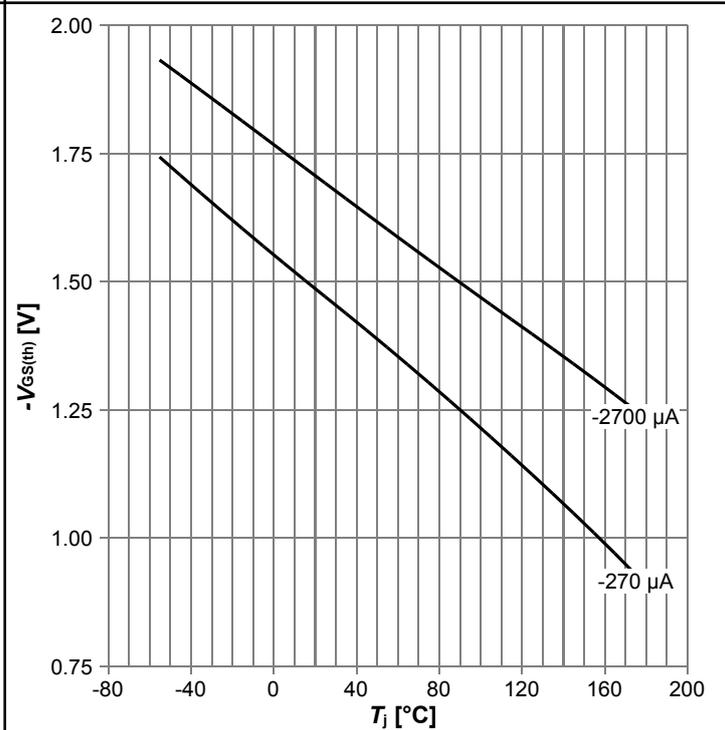
$R_{DS(on)}=f(V_{GS})$, $I_D=-6.5\text{ A}$; parameter: T_j

Diagram 9: Normalized drain-source on resistance



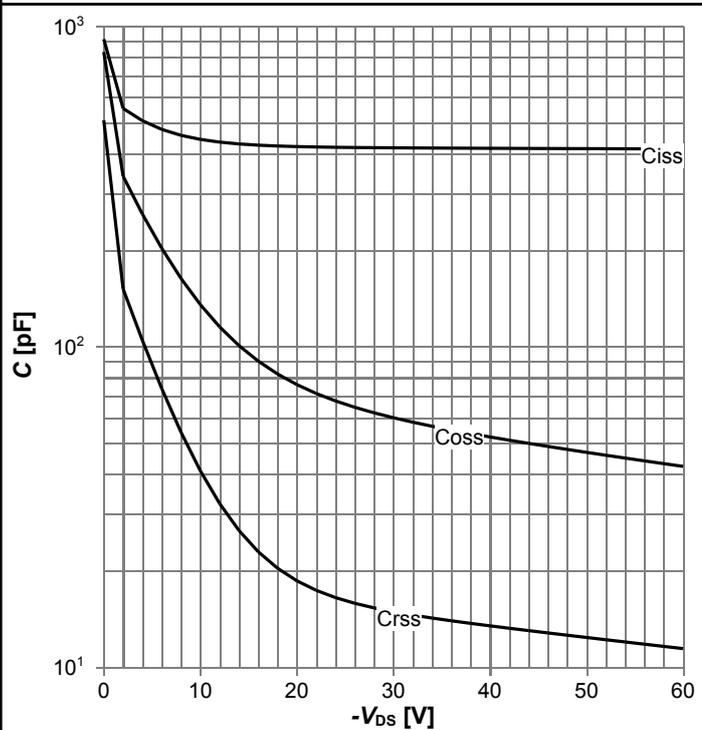
$R_{DS(on)}=f(T_j)$, $I_D=-6.5$ A, $V_{GS}=-10$ V

Diagram 10: Typ. gate threshold voltage



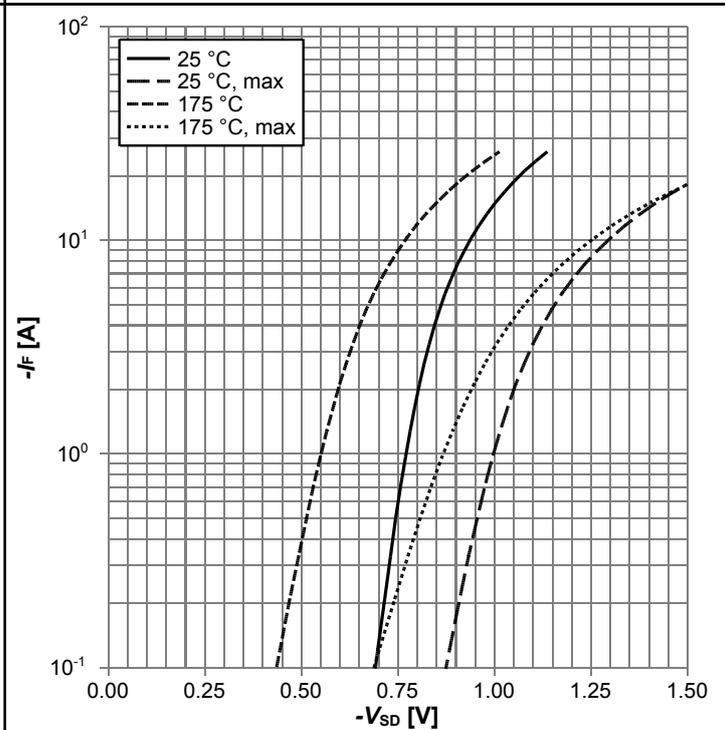
$V_{GS(th)}=f(T_j)$, $V_{GS}=V_{DS}$; parameter: I_D

Diagram 11: Typ. capacitances



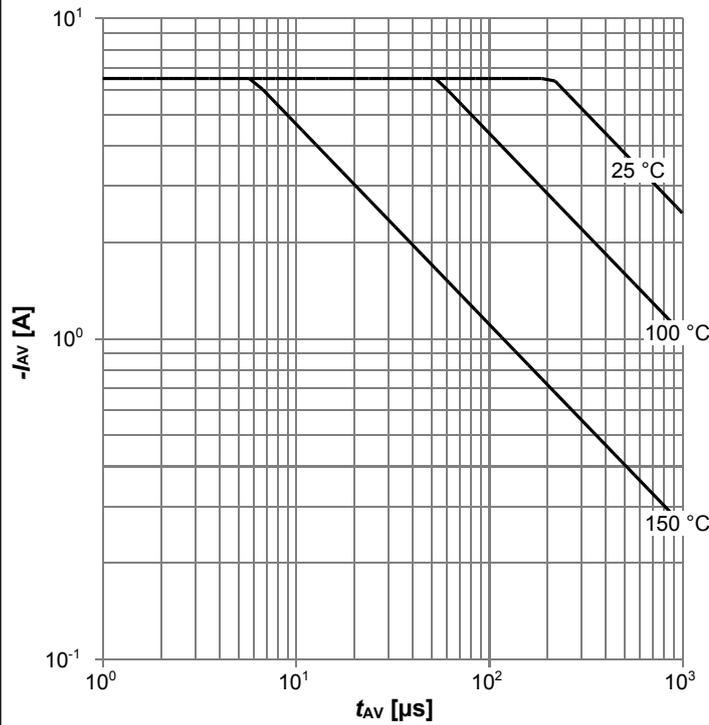
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz

Diagram 12: Forward characteristics of reverse diode



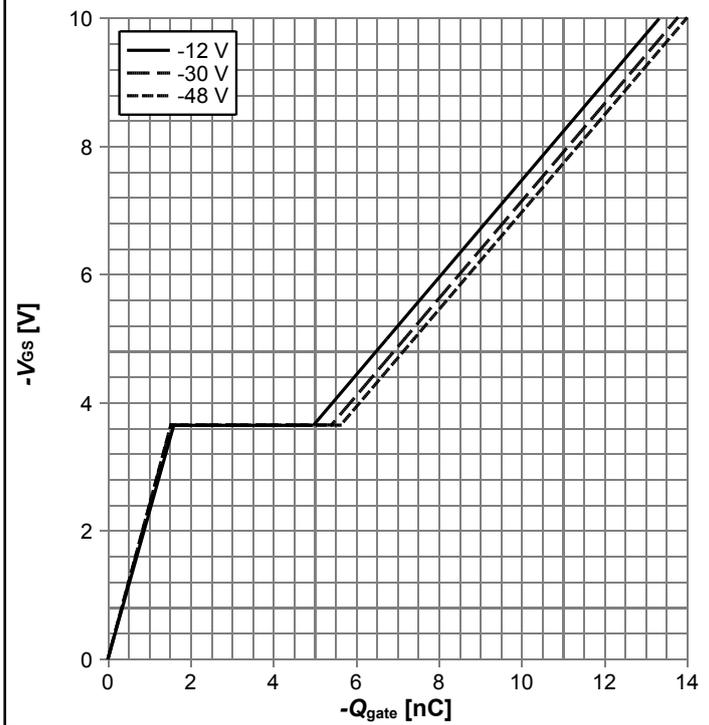
$I_F=f(V_{SD})$; parameter: T_j

Diagram 13: Avalanche characteristics



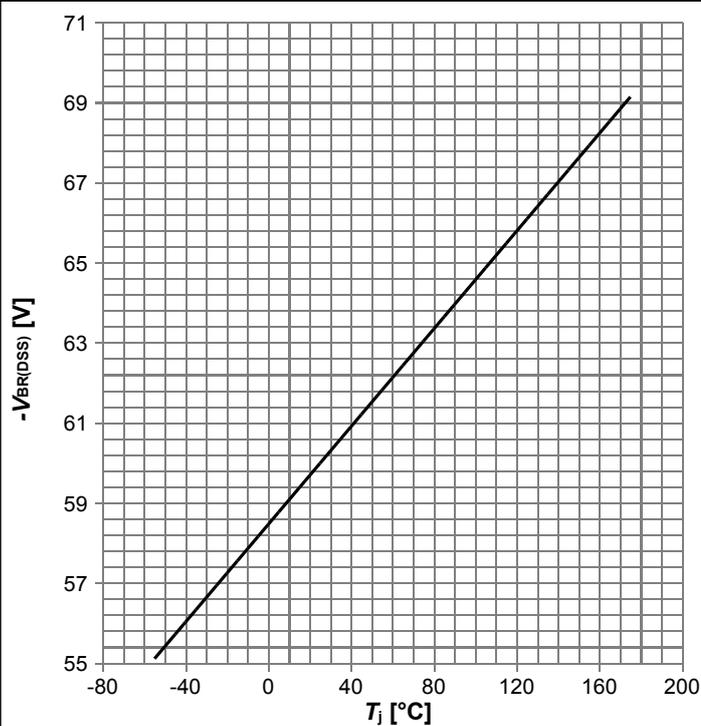
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



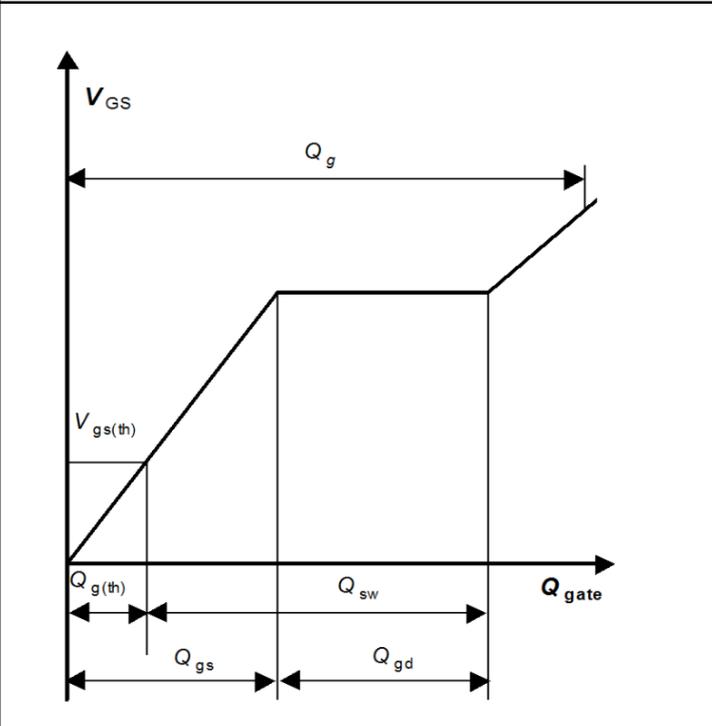
$V_{GS}=f(Q_{gate}), I_D=-6.5$ A pulsed, $T_j=25$ °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

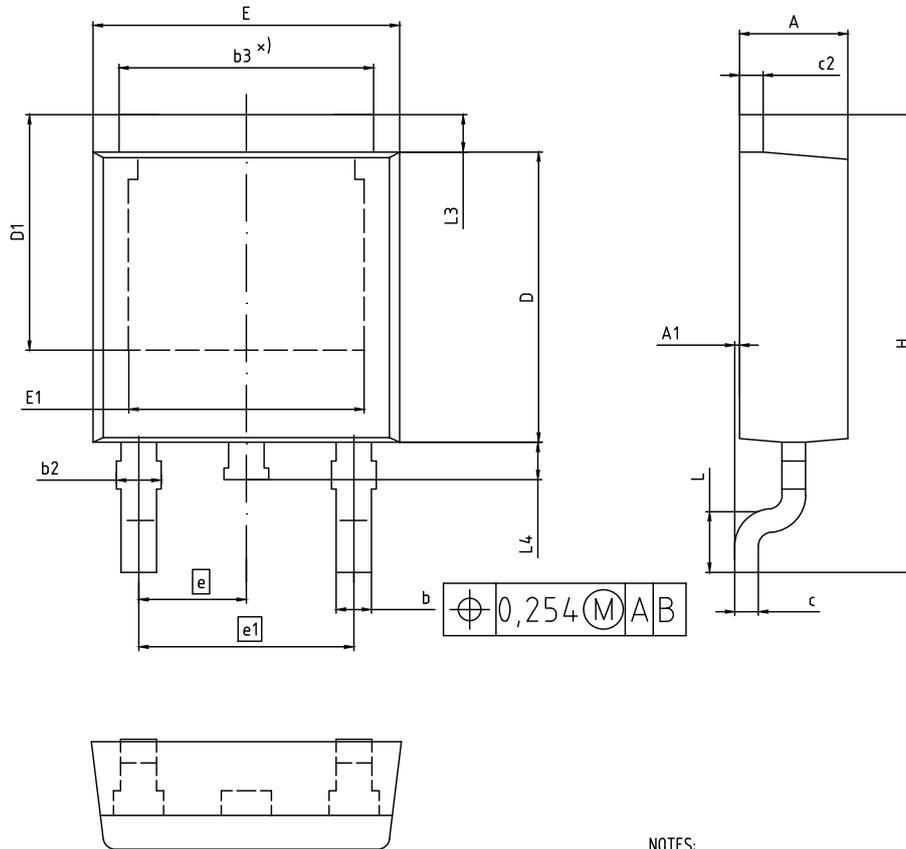


$V_{BR(DSS)}=f(T_j); I_D=-250$ μ A

Diagram Gate charge waveforms



5 Package Outlines



NOTES:

1. INDUSTRIAL QUALITY GRADE
2. ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	4.95	5.50	0.195	0.217
c	0.46	0.61	0.018	0.024
c2	0.40	0.98	0.016	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57 (BSC)		0.180 (BSC)	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.78	0.046	0.070
L3	0.89	1.27	0.035	0.050
L4	0.51	1.02	0.020	0.040

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REVISION 06

Figure 1 Outline PG-TO 252-3, dimensions in mm/inches

Revision History

IPD25DP06LM

Revision: 2019-03-26, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-03-26	Release of final version

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